ELECTRONICS, INC.
44 FARRAND STREET
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NTE552
Silicon Rectifier
General Purpose, Fast Recovery

Features:

- Low Cost
- Low Leakage
- Low Forward Voltage Drop
- High Current Capability
- Supplied in DO41 Package

Maximum Ratings and Electrical Characteristics:

(Ratings at 26°C ambient temperature unless otherwise noted. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%)

Maximum Recurrent Peak Reverse Voltage 600V
Maximum RMS Voltage 420V
Maximum DC Blocking Voltage 600V
Maximum Average Forward Rectified Current (.375” (9.5mm) Lead Length at T_A = +75°C) 1A
Peak Forward Surge Current (8.3ms Single Half Sine–Wave Superimposed on Rated Load) . 50A
Maximum Instantaneous Forward Voltage at 1A DC 1.2V
Maximum DC Reverse Current at Rated DC Blocking Voltage (T_A = +25°C) 5.0µA
Maximum Full Load Reverse Current
(Full Cycle Average (.375” (9.5mm) Lead Length at T_L = +55°C) 100µA
Maximum Reverse Recovery Time (Note 1) 200nS
Typical Junction Capacitance (Note 2) 15pF
Operating Junction Temperature Range, T_J . . . . . –65° to +175°C
Storage Temperature Range, T_{stg} . . . . . –65° to +175°C

Note 1. Reverse Recovery Test Conditions: I_F = 1A, V_R = 30V
Note 2. Measured at 1MHz and applied reverse voltage of 4 volts.